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Research Paper

Failure Investigation of Plastic Shredding Machine's Flange Coupling Based on Mechanical Analysis

Ignatius Pulung Nurprasetio, Bentang Arief Budiman, Farid Triawan (Author)

"124-133 "

 PDF

Use of Carbon Nano-Fibers in Cementitious Mortar

Muhammad Maqbool Sadiq Awan, Parviz Soroushian, Arshad Ali, Muhammad Yousaf Saqid Awan (Author)

134-151

 PDF

Influences of Size and Amount of Colloidal Template and Droplet Diameter on the Formation of Porous-structured Hyaluronic Acid Particles

Asep Bayu Dani Nandiyanto, Kikuo Okuyama (Author)

152-165

 PDF

Process Design and Modelling of the Production of Butyl Cellosolve Acetate and EO-3 Phosphate Ester

Lupete K Bhullar, Zulpan Adi Putra (Author)

166-182



Effect of substrate temperature on quality of copper film catalyst substrate: A Molecular Dynamics Study

Rinaldo Marimpul (Author)

183-190



Synthesis CuInSe₂ (CISE) Thin Films Prepared from Metal-Ethanolamine Complex Compound

Ersan Y Muslih, Agus Ismail, Kyoo Ho Kim (Author)

191-196



Water Level Measurement Altitude Trainer Integrated With Human Machine Interface

Ade Gafar Abdullah, Agung Pramudiantoro Putra (Author)

197-210



Module-scale simulation of forward osmosis module-part B: Modified Spiral-Wound

Muhammad Roil Bilad (Author)

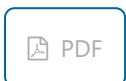
211-220



Mitochondrial Biogenesis Induced by Exercise and Nutrients: Implication for Performance and Health Benefits

Kazumi Masuda, Thomas Jue, Ronald D. Ray Hamidie (Author)

221-229



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Synthesis CuInSe₂ (CISE) Thin Films Prepared from Metal-Ethanolamine Complex Compound

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Abstract

CuInSe₂ (CISE) thin film was successfully fabricated from copper and indium salts with ethanolamine as precursors. All of these precursors were dissolved and formed complex compounds with ethanolamine simultaneously which deposited on soda lime glass by spin coating at 200 rpm, followed by heat treatment in the ambient atmosphere at 200°C for 120 minutes and finally selenization at 550 °C using selenium pellets under Ar (95%) + H₂ (5%) for 120 minutes to fabricate CISE thin film. Reaction mechanism, morphology and electrical properties also reported in this work.

Keyword: CISE, thin film, ethanolamine, complex compound, selenization.

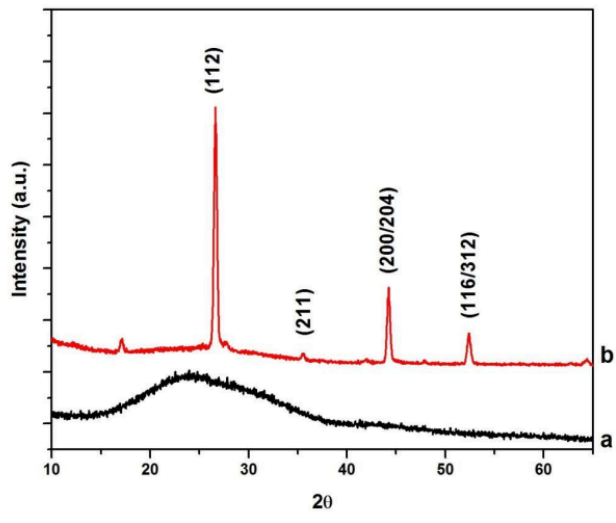
Introduction

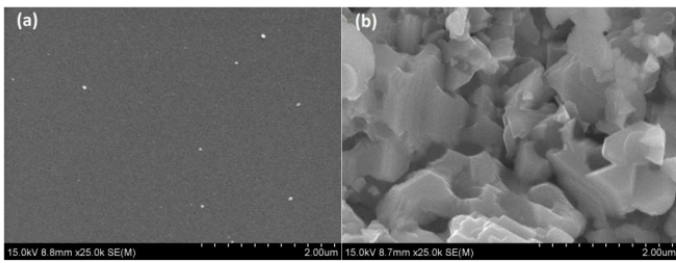
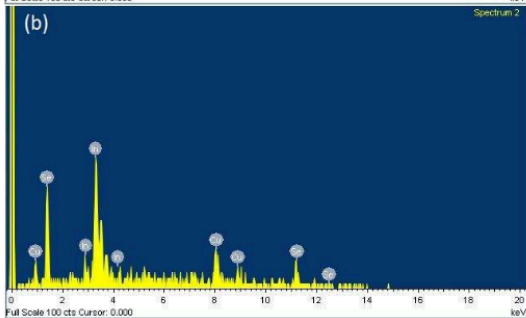
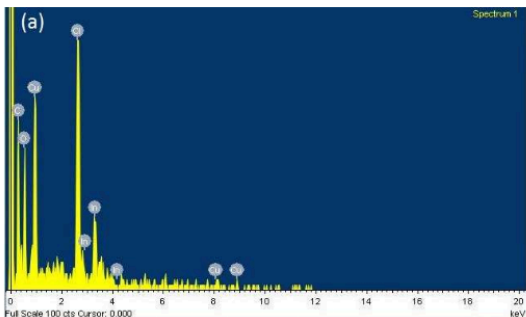
CuInSe₂ (CISE) is an ideal material for thin film solar cell application due to has optimum band gap (1.01 eV) and high absorption coefficient (10⁵ cm⁻¹) [1]. CISE thin films could be prepared by vacuum and non-vacuum methods. However, vacuum process such as chemical process is preferable due to low cost but still get high efficiency [2]. Although chemical process is preferable, this method using harmful solvents such as hydrazine and pyridine [3,4]. Besides that, chemical process could leaves carbon in the thin film as residue [5]. In this work, CISE thin film has been fabricated by chemical process using ethanolamine as a solvent, deposited by spin coating and followed by selenization.

Experimental Detail

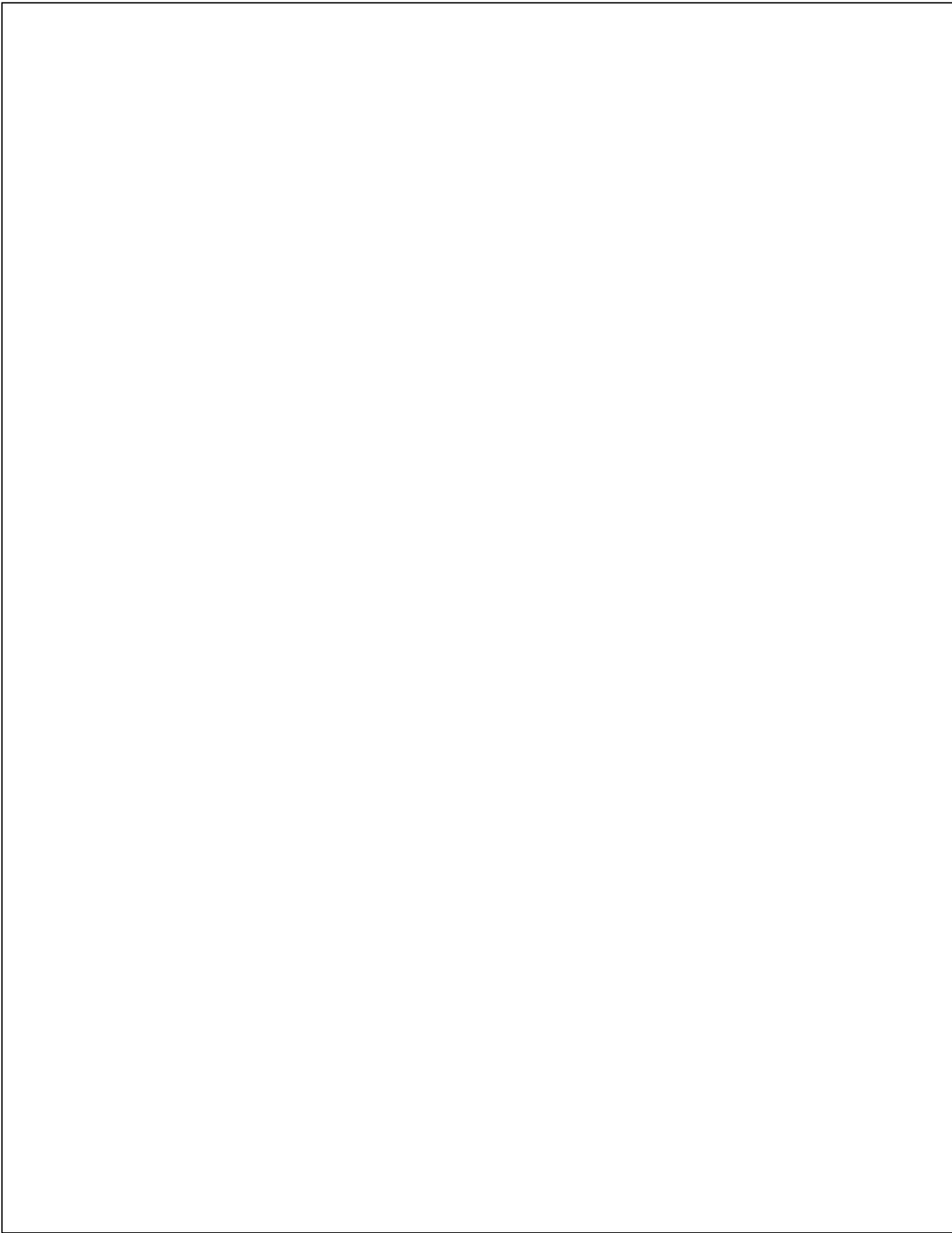
Copper(II) acetate and indium(III) chloride from Aldrich were dissolved in ethanolamine Cu/In molar ratio

Results and Discussion





% Atomic	Before Annealing	After Annealing
Cu		15.68
In		11.60
Se	0.00	24.58
C		0.00
Cu/In ratio		1.35
(Cu+In)/Se ratio		1.11



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Synthesis CuInSe₂ (CISe) Thin Films Prepared from Metal-Ethanolamine Complex Compound

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ABSTRACT

CuInSe₂ (CISe) thin film was successfully fabricated from copper and indium salts with ethanolamine as precursors. All of these precursors were dissolved and formed complex compounds with ethanolamine simultaneously which deposited on soda lime glass by spin coating at 200 rpm, followed by heat treatment in the ambient atmosphere at 200°C for 120 minutes and finally selenization at 550°C using selenium pellets under Ar (95%) + H₂ (5%) for 120 minutes to fabricate CISe thin film. Reaction mechanism, structure, morphology and chemical composition also reported in this work.

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1. INTRODUCTION

CuInSe₂ (CISE) is an ideal material for thin film solar cell application due to has optimum band gap (1.01 eV) and high absorption coefficient (105 cm⁻¹) (Shay *et al.*, 1973; J. Araujo *et al.*, 2007). CISE thin films could be prepared by vacuum and non-vacuum methods. However, non-vacuum process such as chemical process is preferable due to low cost but still get high efficiency (Yin Liu *et al.*, 2012). Although chemical process is preferable, this method using harmful solvents such as hydrazine and pyridine (C.J. Hibberd *et al.*, 2010). Besides that, chemical process could leaves carbon in the thin film as residue (Shanza *et al.*, 2016). In this work, CISE thin film has been fabricated by chemical process using ethanolamine as a solvent, deposited by spin coating and followed by selenization.

There the purpose of this study wa to synthesized CuInSe₂ this film. The material was prepare from copper and indium salts with ethanolamine as precursors

2. EXPERIMENTAL DETAIL

2.1. Materials and Methods

In this work, the precursor solution was made from 0.1 M of copper (from copper(II) acetate) and 0.1 M of indium (from indium(III) chloride) All components were dissolved in 30% ethanolamine (ETA) in ethanol. The solution and exhibited a blue

color when using 1:1 Cu/In ratio. Moreover, 0.05 mL of precursor solution was deposited at 2000 rpm for 10 seconds on soda lime glass (SLG), which cleaned with acetone, ethanol, deionized water using ultrasonic for 15 minutes respectively and dried by nitrogen gas in order to eliminate contaminants further. Subsequently, deposited precursor was dried in tubular furnace at 200°C for 120 minutes until black shinny color was appeared. Repeating the deposition and the heat treatment appropriately can get desirable film thickness. Finally, the CISE thin film obtained by selenization in tubular furnace at 550°C using selenium pellets as selenium source under Ar (95%) + H₂ (5%) atmosphere for 120 minutes. After selenization, the sample was cooled to room temperature under natural cooling condition.

2.2. Characterization of CISE thin film

The morphology was observed by scanning electron microscopy (SEM, Hitachi S4800, Japan). The chemical composition of the films was analyzed by energy dispersive x-ray spectrometry (EDS, Horiba, Japan). The crystal structures were determined by x-ray diffraction (XRD, PANalytical MPD, Netherlands). The absorption spectra were recorded using a UV-Vis-NIR spectrophotometer (Varian Carry 5000, U.S.A). The electrical properties were examined by Hall-Effect measurements using a Van der Paw method (HMS-3000, Ecopia U.S.A.).

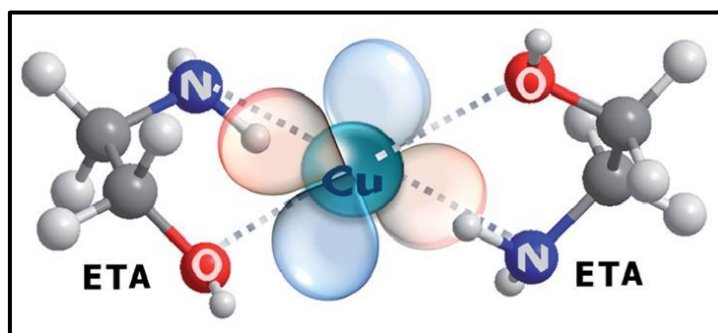
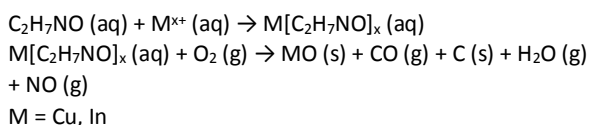


Figure 1. . Illustration of Cu-ETA complex compound (Cho *et al.*, 2014)

3. RESULTS AND DISCUSSION

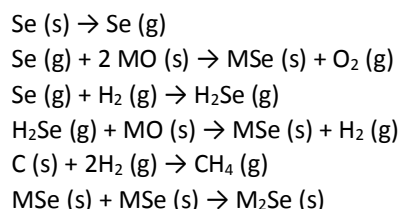
In this work, ethanolamine (ETA) and metal ions such as copper and indium could form a complex compound due to ethanolamine has free electron pair which donated to metal ions and form a coordination or complex bonding where the ETA acts as ligands and the metal ions act as a center atom. Since the unique structure of ETA, thus ETA could act as a chelating agent which illustrated as **Figure 1**.

Moreover, at drying process, Cu-ETA and In-ETA complex compounds were decomposed under air atmosphere into metal oxide. Detailed reaction are



After annealing at 550 °C under Ar (95%) + H₂ (5%) atmosphere for 120 minutes, selenium was changed into vapor phase and then, some of Se vapor was react with metal oxide and H₂ simultaneously. Se vapor reacts with metal oxide and H₂ form metal selenide and H₂Se respectively. Further, H₂Se could react with metal oxide and form metal selenide either. Meanwhile, carbon as

residue reacted with H₂ became methane gas and removed from thin film. Finally, metal selenide such as CuSe and InSe were coalesced into CuInSe₂ as a final product. In other hand, this reaction mechanism shows that H₂ acts as catalyst and as carbon remover simultaneously. Detailed reactions are



Before annealing, x-ray defraction pattern (XRD) shows a broadened peak from 13.75° to 38.48°, which confirmed amorphous phase belong to carbon as dominant compound, while metal oxides due to in amorphous phase could not detected by XRD (see **Figure 2**). After annealed at 550 °C under Ar (95%) + H₂ (5%) atmosphere for 120 minutes, CuInSe₂ has been formed with four peaks at 26.76 °, 35.55 °, 44.25°, and 52.49° which indexed as (112), (211), (200/204), and (116/312) respectively which matched with CuInSe₂ standard (ICDD: 04-005-3912) as tetragonal crystal system.

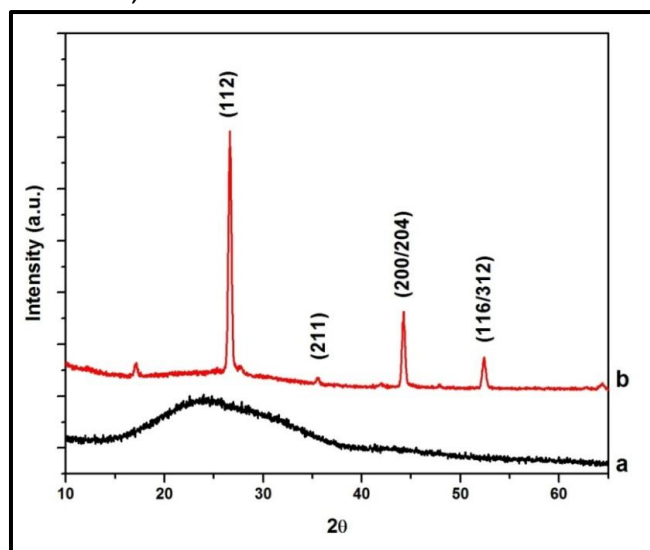


Figure 2. XRD pattern of CuInSe₂ thin film before (a) and after (b) annealing

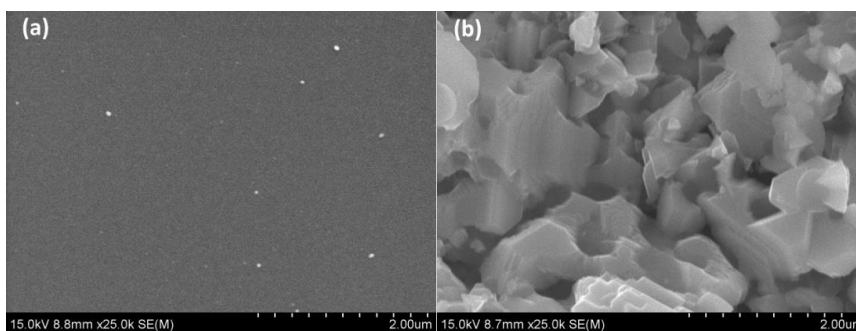


Figure 3. SEM image of CISe before (a) and after (b) annealing

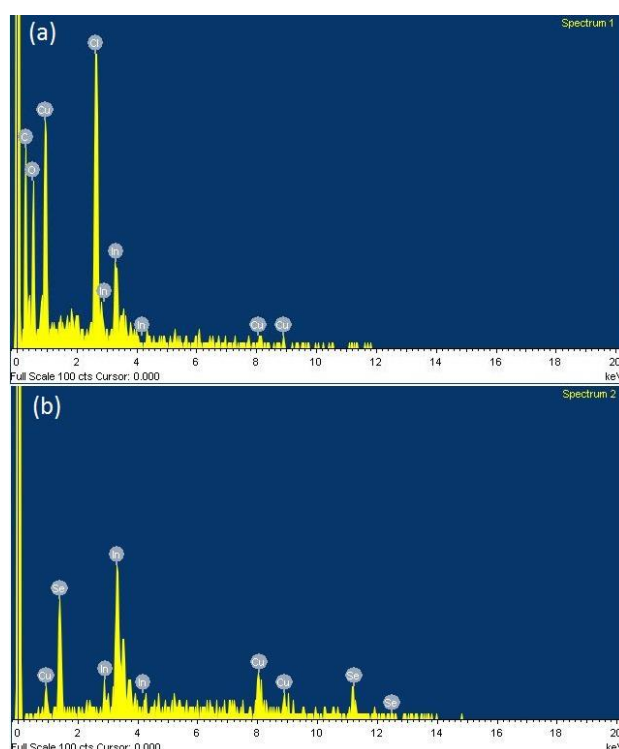


Figure 4. EDS spectrums of CISe before (a) and after (b) annealing

Moreover, scanning electron microscope (SEM) in **Figure 3** shows that the morphology of precursor has smooth and tiny particles spread around the surface. Meanwhile, after annealing, shows the morphology, became larger and compact without shown hexagonal shape from copper was seen. It seems the reaction was going completely.

Organic residue was represented by carbon which existed in the thin film and could be determined by energy dispersive

spectrometry (EDS) (see **Figure 4**). The spectrum shows the proof of carbon existence in the thin film before annealing. In addition to carbon, also could be seen the spectrums of chloride from metal salts, while oxygen could represent of either organic residue or metal oxide. However, after annealing, the EDS spectrums of carbon, chloride and oxygen spectrums were no longer seen in the thin film. It seems they have been removed successfully during annealing

Tabel 1. Chemical composition of CISE thin film before and after

	% Atomic				Ratio	
	Cu	In	Se	C	Cu/In	(Cu+In)/Se
Before Annealing	19.61	16.34	0.00	64.05	1.20	-
After Annealing	15.68	11.60	24.58	0.00	1.35	1.11

EDS also could be used for determining the chemical composition of CISE thin film before and after annealing (see **Table 1**). Before and after annealing Cu/In ratio were 1.20 and 1.35 respectively. The slight enhancement of ratio probably due to diminished of indium in the thin film during annealing considering the melting point of indium (156 °C), which is below the annealing temperature. In other hand, copper is a stable material, thus during annealing it was not much diminished.

4. CONCLUSION

CuInSe₂ (CISE) thin film has been synthesized successfully from metal salts and ethanalamine complex compounds by spin coating and followed by annealing method. Synthesis reaction mechanism of CISE also proposed in this work in order to explain whole process of synthesis from metal salts, complex compounds to CISE thin film. The structure of CISE thin film shows a tetragonal

and matched with CISE standard. Moreover, CISE thin film has a suitable chemical composition with no more carbon or organic residue in the thin film.

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The author(s) declare(s) that there is no conflict of interest regarding the publication of this article. Authors confirmed that the data and the paper are free of plagiarism

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